

GigaDevice Semiconductor Inc.

GD30SP2200x OVP Load Switch with Adjustable OVLO

Datasheet



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1 Features

- 2.5V to 30V Wide Input Voltage Range
- Up to 3A output current
- 100µA Low Quiescent Current
- Internal Fixed OVLO threshold 6.8V
- Wide Adjustable OVLO Threshold Range from 4V to 15V
- Low R_{DS_ON} for Internal Switches :50mΩ
- Fast Turn-off Response time when OVP: 450ns
- Over Temperature Protection
- RoHS Compliant and Halogen Free
- Compact Package: DFN8L(2X2)

2 Applications

- True Wireless Stereo (TWS)
- Bluetooth Speaker
- Portable and mobile devices
- Smart phones
- Low voltage peripherals

3 General description

The GD30SP2200x is an Over-Voltage-Protection (OVP) load switch of $50m\Omega$ with adjustable over-voltage-lock-out (OVLO) threshold voltage. The device will turn off the internal MOSFET switch in a fast response of 450ns when the input voltage is over the pre-set OVLO threshold.

When the OVLO is connected to GND, the internal fixed OVLO threshold is set at 6.8V. The OVLO threshold voltage can be adjusted with an external resistor divider and the range is between 4V and 15V. The IC allows a maximum 3A current from IN to OUT. An over temperature protection (OTP) function is implemented internally and monitors the chip temperature to protect the device.

The GD30SP2200x is available in a green small foot print DFN8L(2X2) package.



4 Device overview

4.1 Device information

Table 4-1 Device Information for GD30SP2200x

Part Number		Package	Function	Description
	GD30SP2200x	DFN8L(2X2)	Over-Voltage-Protection	OVP Load Switch with Adjustable
	GD303P2200X			OVLO

4.2 Block diagram

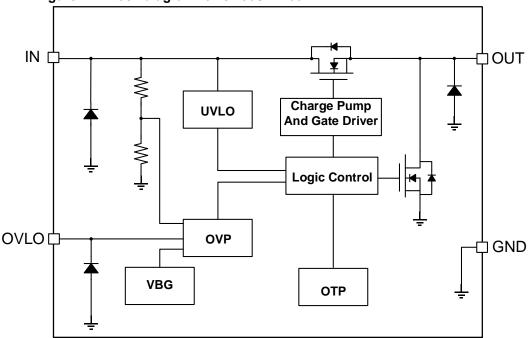
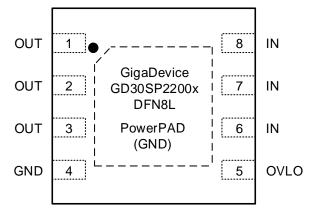


Figure 4-1 Block diagram for GD30SP2200x



4.3 Pinout and pin assignment

Figure 4-2 GD30SP2200x DFN8L(2X2) pinouts



4.4 Pin definitions

Table 4-2. GD30SP2200x DFN8L(2X2) pin definitions

Pin Name	Pins	Pin Type	Functions description
OUT	1,2,3	0	Output of the Regulator . A general 4.7uF ceramic capacitor should be placed as close as possible to this pin.
GND	4	G	Ground . The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.
OVLO	5	I/O	OVLO Threshold Set . Connect a resistor-divider to set different OVLO threshold, $V_{OVLO}=1.2x(1+R1/R2)$ as shown in typical application.
IN	6,7,8		Power Supply Voltage Input . A general 1uF ceramic capacitor should be placed as close as possible to this pin.
PowerPAD	9	G	Thermal pad. connect to ground.

Notes:

(1) Type: I = input, O = output, I/O = input or output, G = Ground.



5 Functional description

5.1 Detailed Description

The GD30SP2200x is placed between the power supply and the low-voltage load to be protected. The device consists of a slew-rate controlled, low resistance OVP switch of typical $50m\Omega$ and over-voltage monitor and protection (OVLO). The device can protect low voltage systems against voltage faults up to 28V. If the input voltage exceeds the OVLO threshold, the internal switch is turned off to prevent damage to downstream components. A 16ms debounce time is built into the device to prevent false turn-on of the internal switch during startup.

In normal operation the OVP switch acts as a slew-rate controlled load switch, connecting and disconnecting the power supply from IN to OUT. A low resistance N-channel MOSFET is utilized to minimize the voltage drop between the voltage source and the load and to reduce power dissipation. When the input voltage is over the programmed OVLO threshold, the device turns off the internal switch in a fast response of 450ns and disconnects the load from the abnormal input, preventing damage to downstream components.

Other protection features implemented in the device include over temperature protection. In the event that the power dissipation causes the IC temperature to exceed its maximum temperature setting, the GD30SP2200x will turn off.

5.1.1 Internal Switch

The GD30SP2200x incorporate an internal N-MOSFET with a 50m Ω (TYP) R_{on}. The MOSFET is driven by an integrated charge pump which generates the necessary voltage above IN.

5.1.2 OVLO threshold

The GD30SP2200x has a 1.2V over-voltage trip reference on the OVLO pin. With a resistordivider on OVLO pin from IN to GND, the over-voltage protection point of IN can be programmed between 4V and 15V. Fixed OVLO threshold is set with an internal resistordivider providing a 6.8V-threshold. To activate the internal fixed OVP, the OVLO pin should be connected to GND.

5.1.3 Protection features

To avoid mis-operation of the device at low input voltages, the GD30SP2200x shuts down at voltages lower than V_{UVLO} with V_{UVLO} -HYS hysteresis.

The GD30SP2200x enters thermal shutdown once the junction temperature exceeds typically T_{OT} . Once the device temperature falls below the threshold with hysteresis, the device returns



to normal operation automatically.

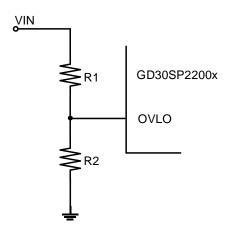
5.2 Application information

5.2.1 OVLO threshold set up

If OVLO is connected to ground, the internal OVLO comparator uses the internally set OVLO value. Once the OVLO pin voltage exceeds the OVLO select voltage, V_{OVLO_SELECT}, an external resistor divider is used to set the OVLO threshold. By selecting R1 and R2, the OVLO voltage is programmed to the desired value.

$$V_{OVLO} = 1.2 \times (1 + \frac{R_1}{R_2})$$

Figure 5-1 Feedback resistor divider



Note1: R1 and R2 are only required for external ovp, otherwise connect OVLO to GND Note2: Recommend 10K≤R2≤50K; add unidirection TVS close to VIN

5.2.2 Input capacitor selection

A 1 μ F or larger capacitor is typically recommended for C_{IN}. C_{IN} should be located close to the device IN pin. Ceramic capacitors are recommended for C_{IN}. Select capacitors with a voltage rating at least 5V higher than the maximum possible voltage during surge. The 50V- rated capacitors are ideal for most applications.

5.2.3 Output capacitor selection

In order to ensure stability while the current limit is active, a small output capacitance of approximately 4.7μ F is required at the output. The output capacitor has no specific capacitor ESR requirement. If desired, C_{OUT} may be increased to accommodate any load transient condition.





6 Electrical characteristics

6.1 Absolute maximum ratings

The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

Symbol	I Parameter		Max	Unit
VIN	Power supply pin	-0.3	30	V
Vout	Output	-0.3	VIN+0.3	V
V _{OVLO}	LO OVLO trip voltage setting		17	V
I _{IN}	Continuous current		3	А
	Thermal characteristics			
TJ	T _J Operating junction temperature		150	°C
T _{stg}	Storage temperature		150	°C
P _{max}	Maximum power dissipation @T _A =25°C		0.5	W

Table 6-1 Absolute maximum ratings

6.2 Recommended operation conditions

Table 6-2 Recommended operation conditions

Symbol	Symbol Parameter		Тур	Max	Unit		
Vin	V _{IN} Power supply pin			28	V		
Vovlo	VovLo OVLO trip		_	5	V		
	Thermal characteristics						
TA	T _A Operating ambient temperature		_	85	°C		
TJ	TJ Operating junction temperature		_	125	°C		

6.3 Electrical sensitivity

The device is strained in order to determine its performance in terms of electrical sensitivity. Electrostatic discharges (ESD) are applied directly to the pins of the sample. Static latch-up (LU) test is based on I-test methods.

Table 6-3 Electrostatic	Discharge	and Latch-up	o characteristics

Symbol	Parameter	Conditions	Value	Unit
M	Electrostatic discharge	T _A = 25 °C;	4000	V
VESD(HBM)	voltage (human body model)	JS-001-2017	±4000	V



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Symbol	Parameter	Conditions	Value	Unit	
	Electrostatic discharge	T _A = 25 °C;	- 2000	V	
Vesd(cdm)	voltage (charge device model)	JS-002-2018	±2000	v	
Lotob up		T _A = 25 °C;	200	m /	
Latch up	l-test	JESD78E	200	mA	

6.4 Power supplies voltages and currents

Table 6-4 Power supplies voltages and currents

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
lq	Quiescent current	V_{IN} = 5V, No switching, T _J =25°C	_	100	_	μA
t _{OVP}	OVP Turn-off time	$V_{IN} > V_{OVLO}, C_{IN}=C_L=0pF$		450		ns
	Over voltage lockout		1.17	1.2	1.00	V
Vovlo_th	reference	—	1.17	1.2	1.23	v
Vovlo_	Over voltage lockout			35		mV
HYS	reference hysteresis	_		55		IIIV
V _{OVLO}	Range of OVLO threshold	—	4	_	15	V
l _{iN}	Maximum through current	—		_	3	А
Ron	Internal switch ON	V _{IN} = 5V, I _{OUT} =1A	_	50	—	mΩ
NON	resistance	VIN - 3V, 1001-1A				
ton	Turn-on time	VIN>VUVLO to VOUT=VIN*90% CL=0		16	_	ms
VUVLO	VIN under voltage lockout	V _{IN} rising		2.25	2.37	V
Vuvlo	VIN under voltage lockout	V _{IN} rising to falling threshold		250		mV
_HYS	hysteresis			230		111V
V _{OVLO_SE}	External OVLO select			0.05		V
LECT	Threshold	_		0.25		v

6.5 **Protections**

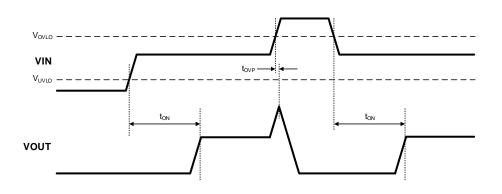
Table 6-5 Over temperature characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{OT}	Thermal shutdown temperature	Die temperature, TJ	135	150	165	°C
T _{HYS}	Thermal hysteresis	Die temperature, TJ	_	20	_	°C

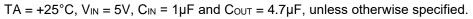


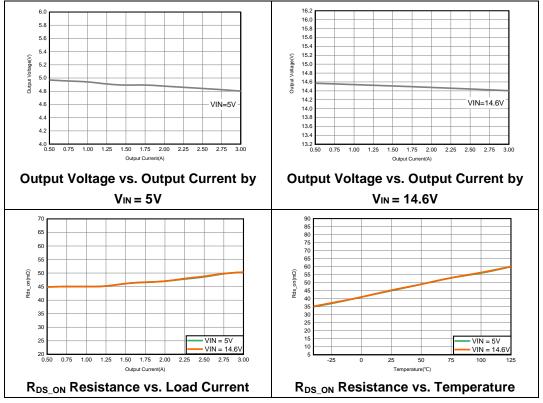
6.6 Timing Diagram

Figure 6-1 Timing Diagram



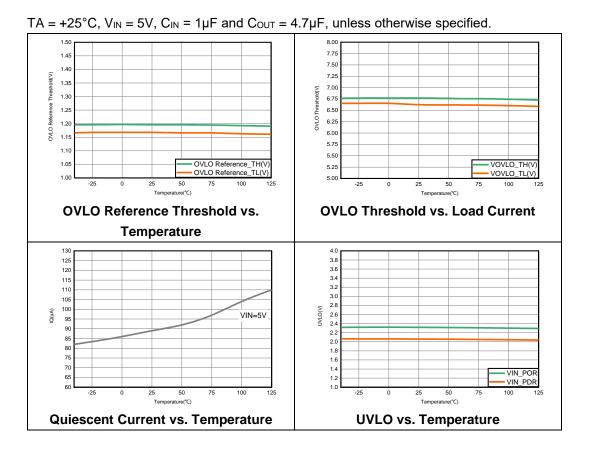
6.7 Typical Characteristics





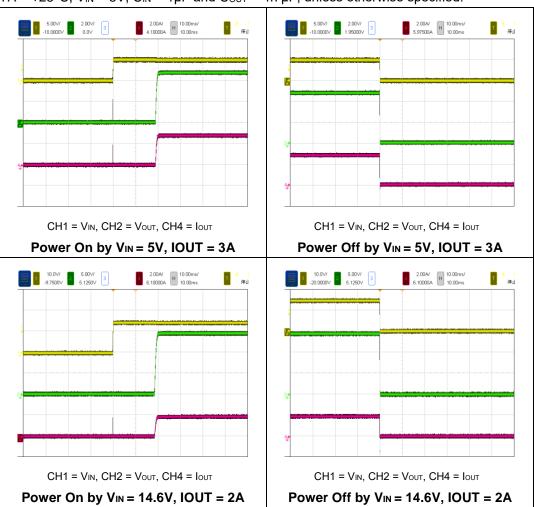


Typical Characteristics





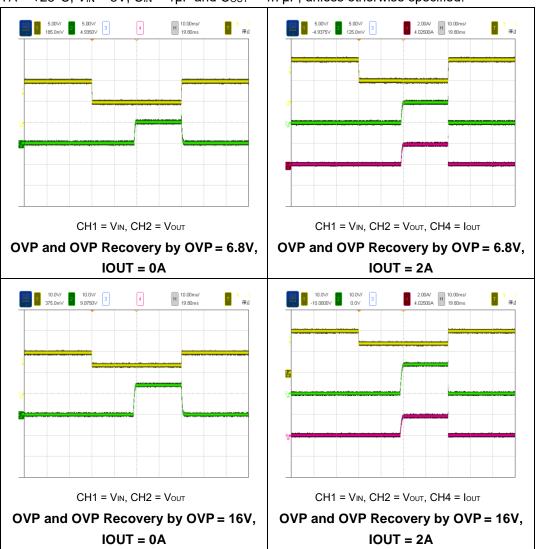
Typical Characteristics



TA = +25°C, V_{IN} = 5V, C_{IN} = 1µF and C_{OUT} = 4.7µF, unless otherwise specified.



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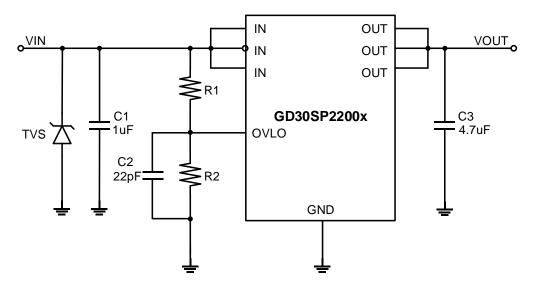


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Typical application circuit

Figure 7-1 Typical GD30SP2200x Application Circuit

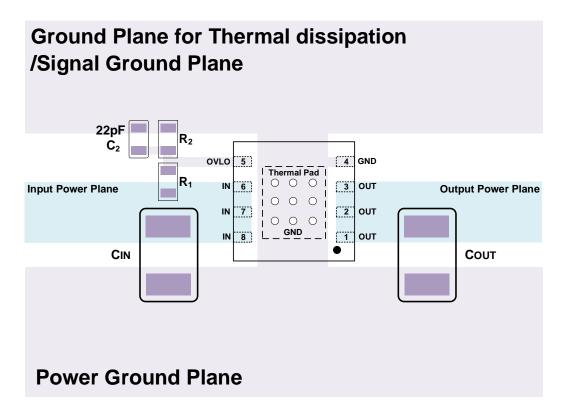
The over-voltage protection with external OVLO Threshold setting.





8 Layout guideline

To make fully use of the performance of GD30SP2200x, the guidelines below should be followed.



1. All the peripherals should be placed as close to the device as possible. Place the input capacitor C_{IN} on the top layer (same layer as the GD30SP2200x) and close to IN pin, and place the output capacitor C_{OUT} on the top layer(same layer as the GD30SP2200x) and close to OUT pin.

2. IN pin routing passes through the external TVS firstly, and then connect GD30SP2200x.

3. If R1 and R2 are used, route OVLO line on PCB as short as possible to reduce parasitic capacitance.



9 Package information

9.1 DFN8L(2X2) package outline dimensions

Figure 9-1 DFN8L(2X2) package outline

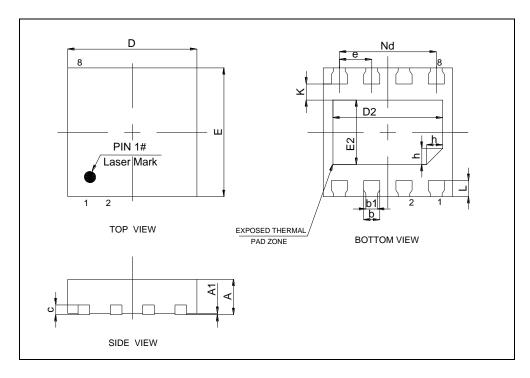
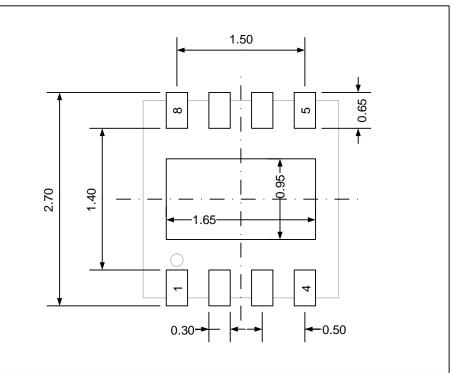


Table 9-1	DFN8L(2X2)	package	dimensions	(in mm)
		P		···· · ····/

Symbol	Min	Тур	Max
A	0.50	0.55	0.60
A1	0	0.02	0.05
b	0.20	0.25	0.30
b1	—	0.18	—
с	—	0.152	—
D	1.90	2.00	2.10
D2	1.60	1.70	1.80
E	1.90	2.00	2.10
E2	0.90	1.00	1.10
е	—	0.50	—
h	0.20	0.25	0.30
К	—	0.25	—
L	0.20	0.25	0.30
Nd		1.50	



Figure 9-2 DFN8L(2X2) recommended footprint



(Original dimensions are in millimeters)

9.2 Thermal characteristics

Thermal resistance is used to characterize the thermal performance of the package device, which is represented by the Greek letter " Θ ". For semiconductor devices, thermal resistance represents the steady-state temperature rise of the chip junction due to the heat dissipated on the chip surface.

- Θ_{JA}: Thermal resistance, junction-to-ambient.
- Θ_{JB}: Thermal resistance, junction-to-board.
- Θ_{JC} : Thermal resistance, junction-to-case.
- Ψ_{JB} : Thermal characterization parameter, junction-to-board.

 Ψ_{JT} : Thermal characterization parameter, junction-to-top center.

 $\Theta_{JA} = (T_J - T_A)/P_D$

$$\Theta_{JB} = (T_J - T_B)/P_D$$

 $\Theta_{JC} = (T_J - T_C)/P_D$

Where, T_J = Junction temperature.

- T_A = Ambient temperature
- T_B = Board temperature
- T_{C} = Case temperature which is monitoring on package surface
- P_D = Total power dissipation

 Θ_{JA} represents the resistance of the heat flows from the heating junction to ambient air. It is an indicator of package heat dissipation capability. Lower Θ_{JA} can be considerate as better



overall thermal performance. Θ_{JA} is generally used to estimate junction temperature. Θ_{JB} is used to measure the heat flow resistance between the chip surface and the PCB board.

 Θ_{JC} represents the thermal resistance between the chip surface and the package top case. Θ_{JC} is mainly used to estimate the heat dissipation of the system (using heat sink or other heat dissipation methods outside the device package).

Table 9-2 Package	e Thermal Characteristics ⁽¹⁾
-------------------	--

Symbol	Condition	Package	Value	Unit
Θја	Natural convection, 2S2P PCB	DFN8L	86.45	°C/W
Θјв	Cold plate, 2S2P PCB	DFN8L	36.25	°C/W
OrO	Cold plate, 2S2P PCB	DFN8L	47.13	°C/W
ψ_{JB}	Natural convection, 2S2P PCB	DFN8L	36.20	°C/W
Ψ_{JT}	Natural convection, 2S2P PCB	DFN8L	3.61	°C/W

(1) Thermal characteristics are based on simulation, and meet JEDEC specification.

(2) The PCB board is JEDEC standard 2S2P FR-4 PCB board, the PCB Dimension(LXM) 114.3X76.2mm, the PCB thickness 1.6mm, 1oz copper.

(3) Power dissipation is calculated by $P_D = (V_{IN}-V_{OUT}) \times I_{OUT}$.



10 Ordering information

Table 10-1 Part order code for GD30SP2200x devices

Ordering Code	Package	Package Type	Packing Type	MOQ	Temperature Operating Range
GD30SP2200WFTR	DFN8L(2X2)	Green	Tape&Reel	3000	–40°C to +85°C



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